

HAT2200WP

Silicon N Channel Power MOS FET Power Switching

REJ03G1678-0300

Rev.3.00

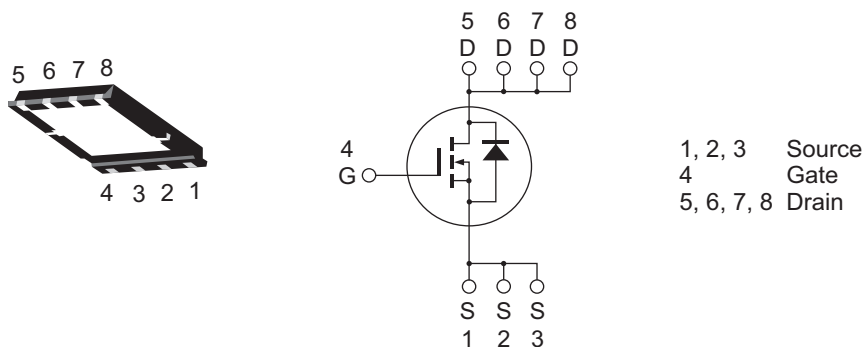
May 27, 2008

Features

- Capable of 8 V gate drive
 - Low drive current
 - High density mounting
 - Low on-resistance
- $R_{DS(on)} = 22 \text{ m}\Omega$ typ. (at $V_{GS} = 10 \text{ V}$)

Outline

RENESAS Package code: PWSN0008DA-A
(Package name: WPAK)



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	100	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	20	A
Drain peak current	$I_{D(pulse)}$ ^{Note 1}	80	A
Body-drain diode reverse drain current	I_{DR}	20	A
Avalanche current	I_{AP} ^{Note 2}	20	A
Avalanche energy	E_{AR} ^{Note 2}	40	mJ
Channel dissipation	P_{ch} ^{Note 3}	20	W
Channel to case thermal Impedance	θ_{ch-c} ^{Note 3}	6.25	°C/W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50 \Omega$
3. $T_c = 25^\circ C$

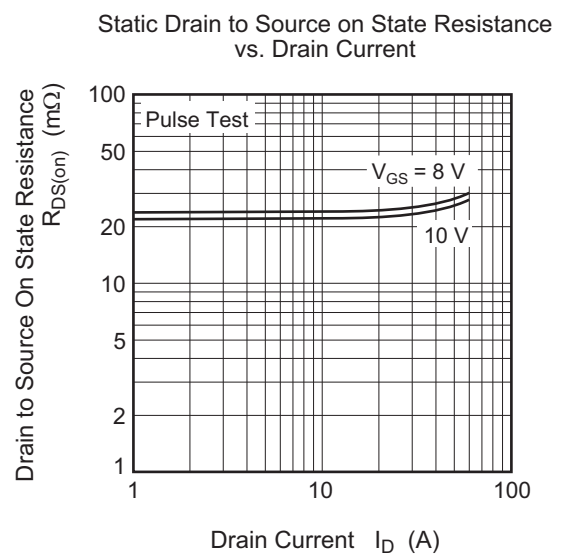
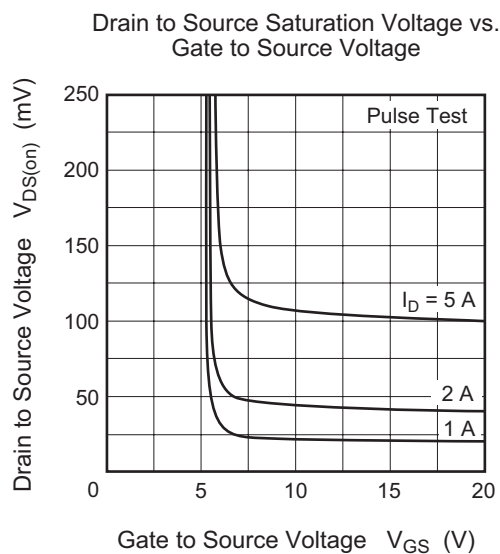
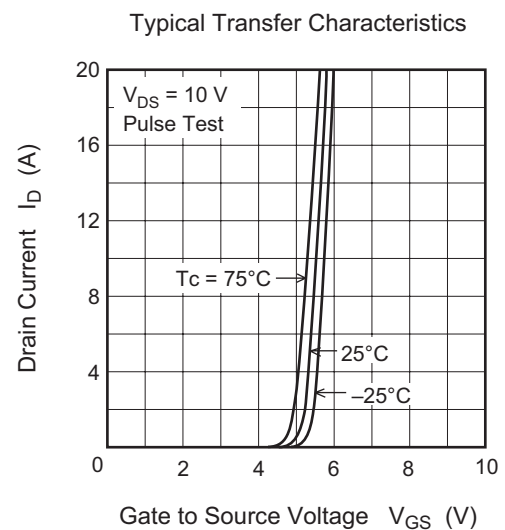
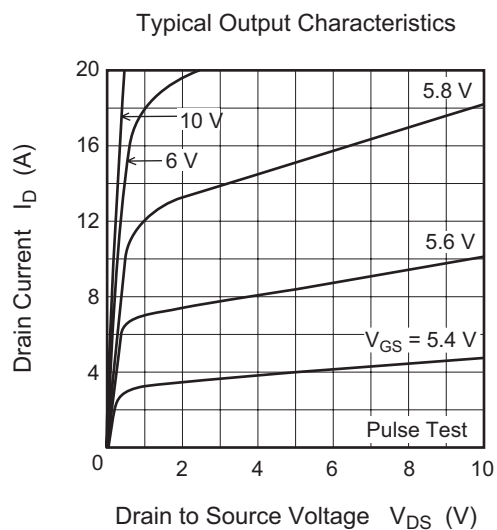
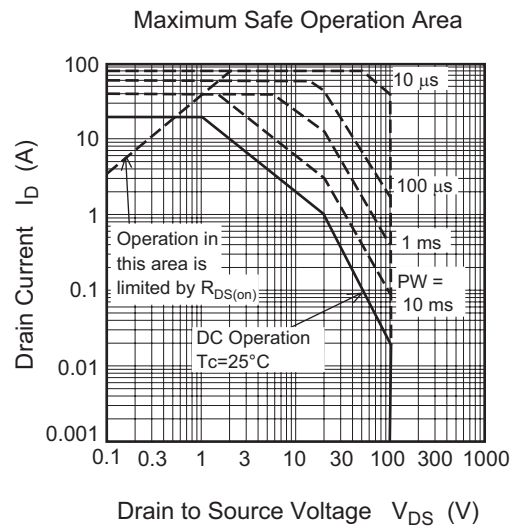
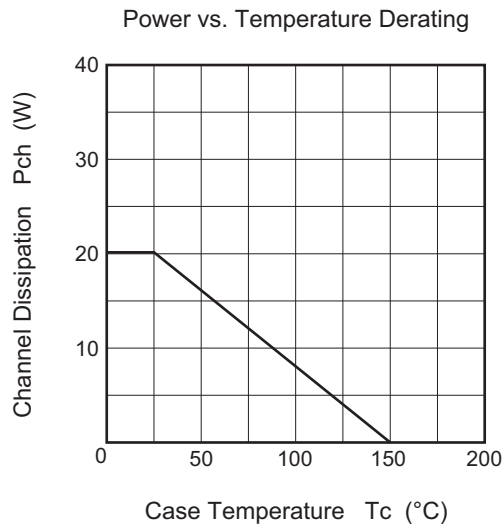
Electrical Characteristics

(Ta = 25°C)

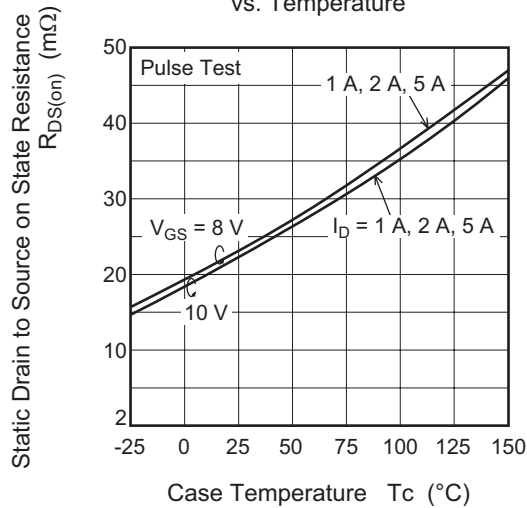
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 100 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.5	—	5.0	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	22	28	$\text{m}\Omega$	$I_D = 10 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	23	33	$\text{m}\Omega$	$I_D = 10 \text{ A}$, $V_{GS} = 8 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	19	33	—	S	$I_D = 10 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	2300	—	pF	$V_{DS} = 10 \text{ V}$ $V_{GS} = 0$ $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	280	—	pF	
Reverse transfer capacitance	C_{rss}	—	90	—	pF	
Gate resistance	R_g	—	1.3	—	Ω	
Total gate charge	Q_g	—	32	—	nc	$V_{DD} = 50 \text{ V}$ $V_{GS} = 10 \text{ V}$ $I_D = 20 \text{ A}$
Gate to source charge	Q_{gs}	—	12	—	nc	
Gate to drain charge	Q_{gd}	—	8	—	nc	
Turn-on delay time	$t_{d(on)}$	—	16	—	ns	$V_{GS} = 10 \text{ V}$, $I_D = 10 \text{ A}$ $V_{DD} \approx 30 \text{ V}$ $R_L = 3 \Omega$ $R_g = 4.7 \Omega$
Rise time	t_r	—	9.5	—	ns	
Turn-off delay time	$t_{d(off)}$	—	31	—	ns	
Fall time	t_f	—	4.6	—	ns	
Body-drain diode forward voltage	V_{DF}	—	0.82	1.07	V	$I_F = 20 \text{ A}$, $V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	50	—	ns	$I_F = 20 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

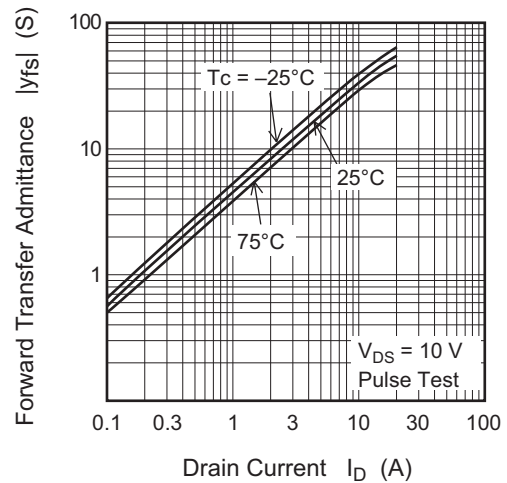
Main Characteristics



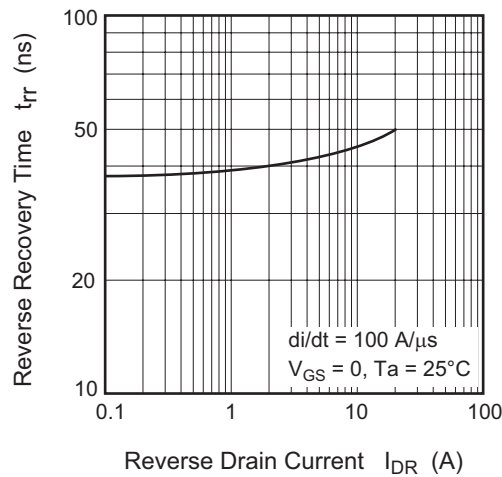
Static Drain to Source on State Resistance vs. Temperature



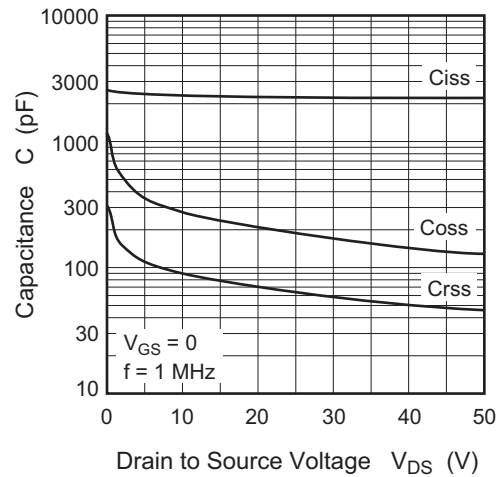
Forward Transfer Admittance vs. Drain Current



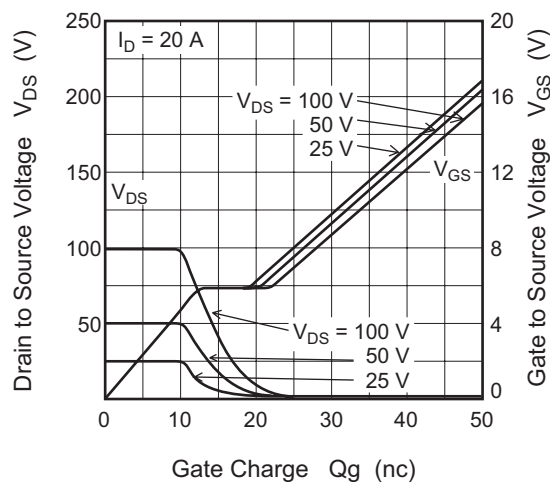
Body-Drain Diode Reverse Recovery Time



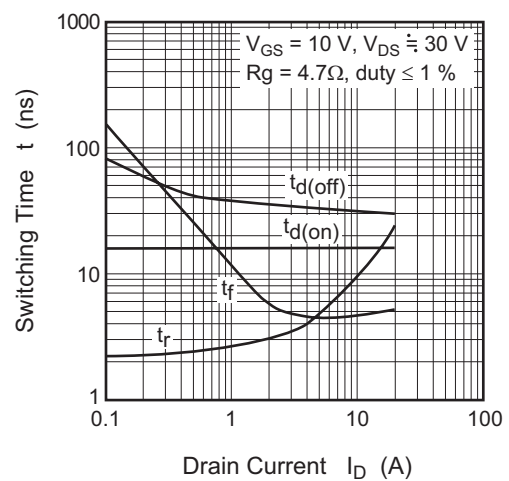
Typical Capacitance vs. Drain to Source Voltage

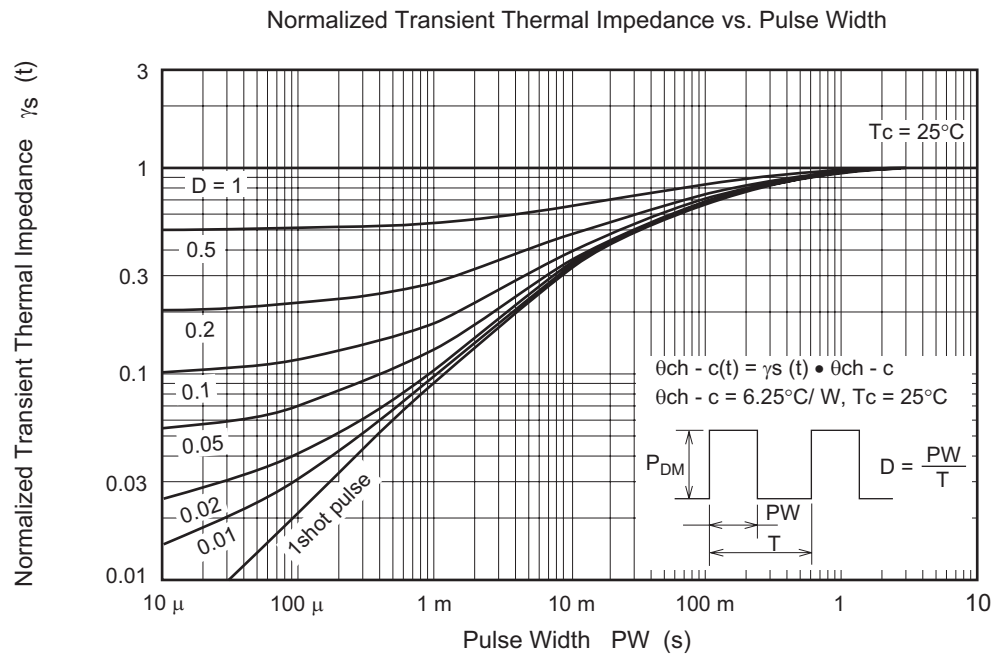
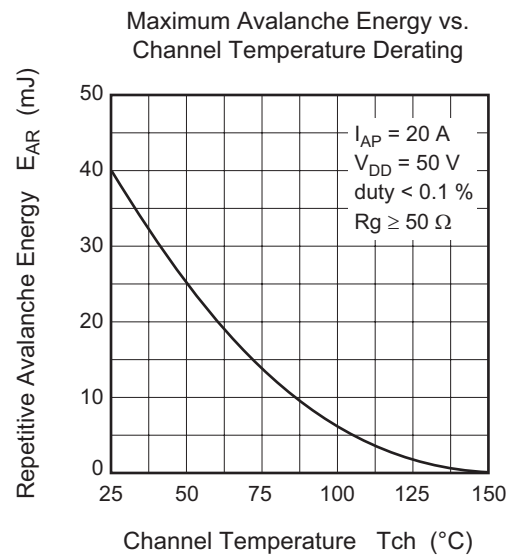
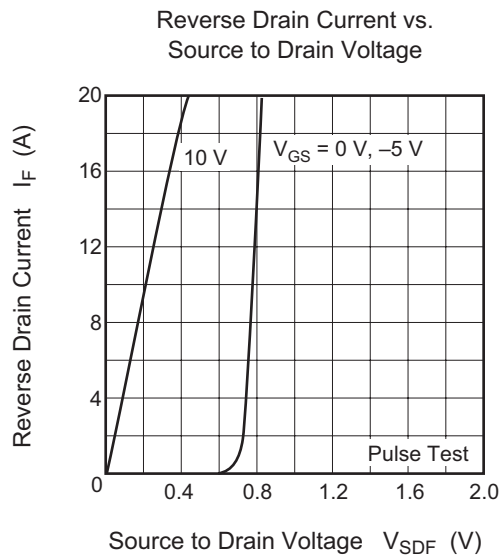


Dynamic Input Characteristics

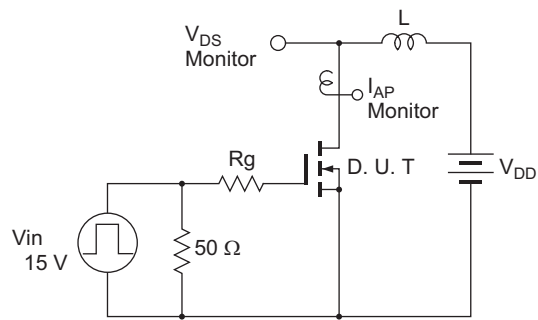


Switching Characteristics



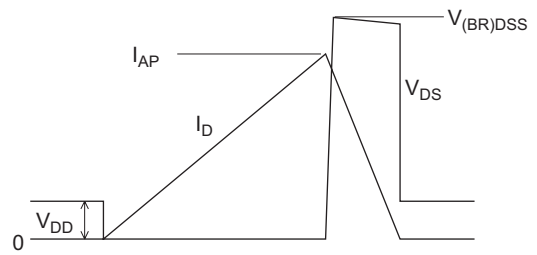


Avalanche Test Circuit

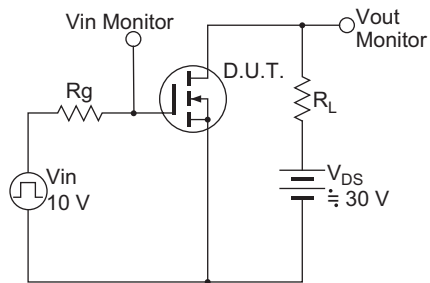


Avalanche Waveform

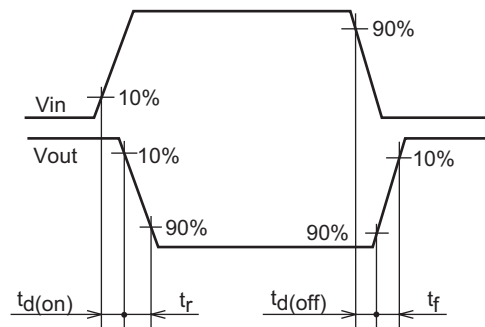
$$E_{AR} = \frac{1}{2} L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



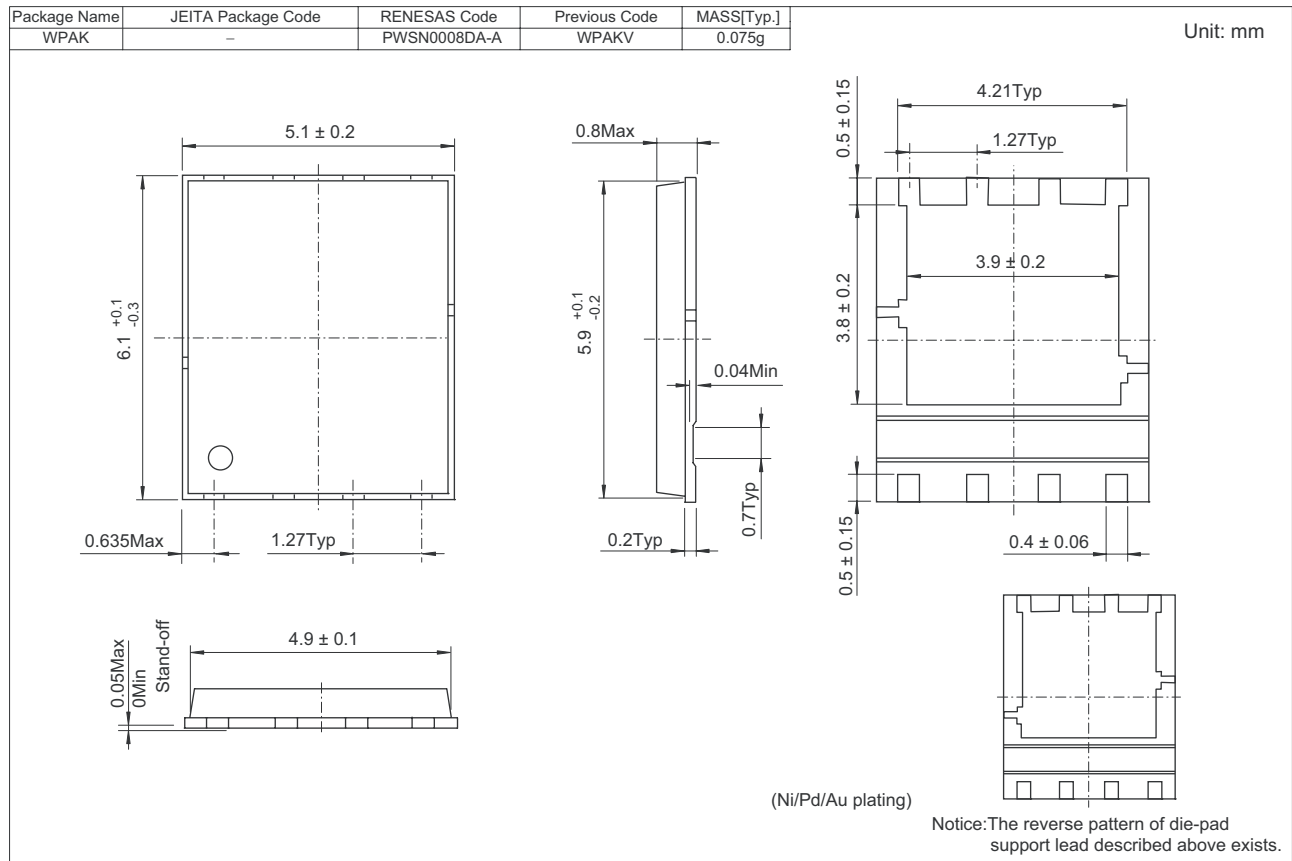
Switching Time Test Circuit



Switching Time Waveform



Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
HAT2200WP-EL-E	2500 pcs	Taping

Notes:

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